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(74) Agents: BIGEL, Mitchell, S. et al.; Myers, Bigel, Sibley,

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- (71) Applicant: THUNDERBIRD TECHNOLOGIES, INC. [US/US]; 1000 Perimeter Park Drive, P.O. Box 13739, Research Triangle Park, NC 27709-3739 (US).
- (72) Inventors: RICHARDS, William, R., Jr.; 200 Meadow Drive, Cary, NC 27511 (US). DENNEN, Michael, W.; 8820 Windjammer Drive, Raleigh, NC 27615 (US).

- & Sajovec, P.A., P.O. Box 37428, Raleigh, NC 27627 (US).
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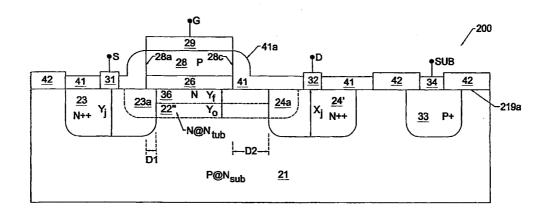
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For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: OFFSET DRAIN FERMI-THRESHOLD FIELD EFFECT TRANSISTORS



(57) Abstract: An offset drain Fermi-threshold field effect transistor (Fermi-FET) includes spaced apart source and drain regions in an integrated circuit substrate, and a Fermi-FET channel in the integrated circuit substrate, between the spaced apart source and drain regions. A gate insulating layer is on the integrated circuit substrate between the spaced apart source and drain regions, and a gate electrode is on the gate insulating layer. The gate electrode is closer to the source region than to the drain region. Stated differently, the drain region is spaced farther away from the gate electrode than the source region. The offset drain Fermi-FET can introduce a drift region between the drain region and the Fermi-FET channel that can provide the high voltage and/or high frequency Fermi-FETs, while retaining the Fermi-FET advantages in the channel.

### INTERNATIONAL SEARCH REPORT

Inter anal Application No PCT/US 99/26046

A. CLA	SSIFIC	ATION	OF	SUBJECT	MATTER
IPC	7	H01L	.29	/78	

According to International Patent Classification (IPC) or to both national classification and IPC

#### B. FIELDS SEARCHED

 $\begin{array}{ll} \mbox{Minimum documentation searched (classification system followed by classification symbols)} \\ \mbox{IPC 7} & \mbox{H01L} \end{array}$ 

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

#### EPO-Internal

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Category °	Citation of document, with indication, where appropriate, of	ane reievani passages	
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	ent referring to an oral disclosure, use, exhibition or means	ments, such combination be	eing obvious to a person skilled

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Name and mailing address of the ISA

Date of the actual completion of the international search

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Inter anal Application No
PCT/US 99/26046

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Citation of document, with indication, where appropriate, of the relevant passages	nelevant to cidim No.
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